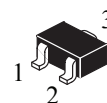


PNP TRANSISTOR

 **Lead(Pb)-Free**

FEATURES:

- * High voltage and high current
- * Excellent hFE linearity
- * Complementary to 2SC4738


SOT-523(SC-75)
MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Units
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current Continuous	I_C	-150	mA
Total Device Dissipation	P_D	100	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	125	$^{\circ}\text{C}/\text{W}$
Junction Temperature	T_J	-55 to +125	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-55 to +125	$^{\circ}\text{C}$

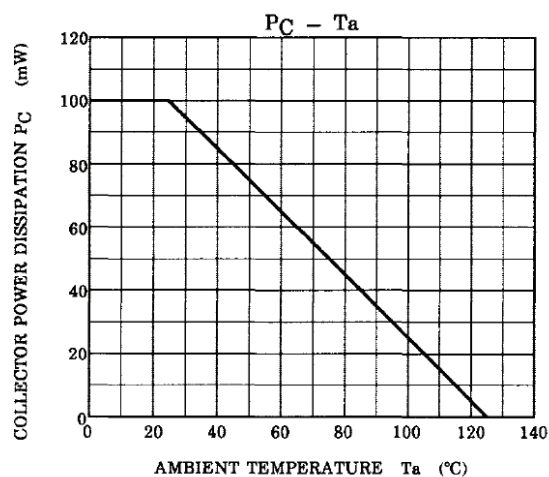
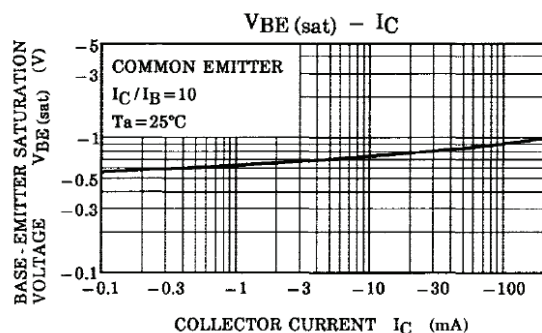
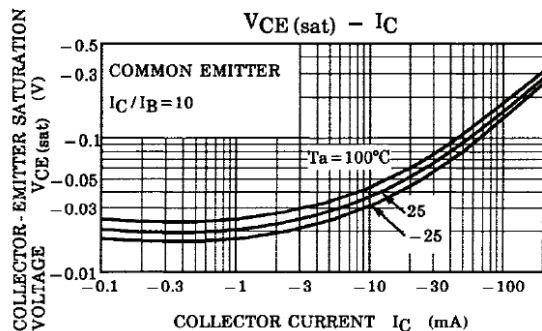
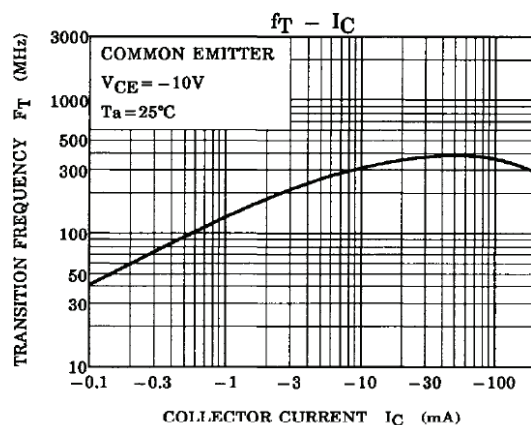
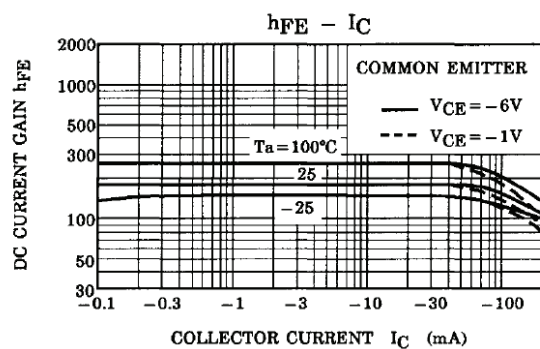
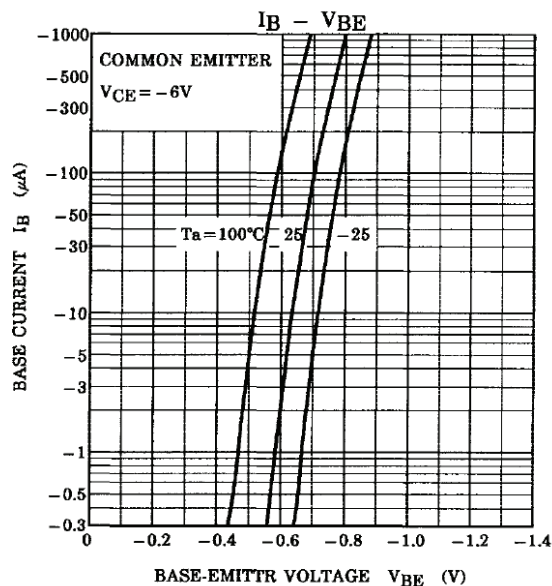
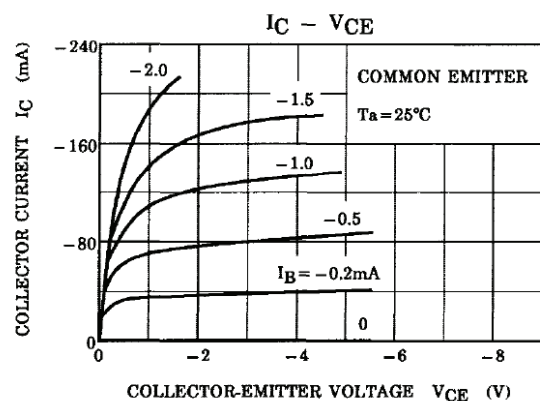
ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V_{CBO}	$I_C=-100\mu\text{A}, I_E=0$	-50			V
Collector-emitter breakdown voltage	V_{CEO}^*	$I_C=-1\text{mA}, I_B=0$	-50			V
Emitter-base breakdown voltage	V_{EBO}	$I_E=-100\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-50\text{V}, I_E=0$			-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$			-100	nA
DC current gain	h_{FE}	$V_{CE}=-6\text{V}, I_C=-2\text{mA}$	120		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100\text{mA}, I_B=-10\text{mA}$			-0.3	V
Transition frequency	f_T	$V_{CE}=-10\text{V}, I_C=-1\text{mA}$	80			MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		4	7	pF

CLASSIFICATION OF h_{FE}

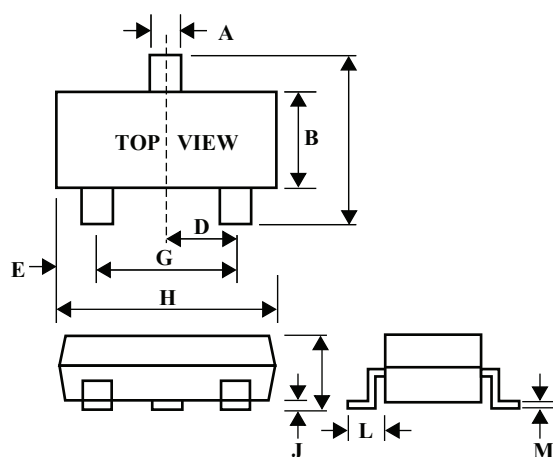
Rank	Y	GR
Range	120-240	200-400
Marking	SY	SG

Typical Characteristics



SOT-523 Outline Dimensions (SC-75)

Unit:mm



SOT-523		
Dim	Min	Max
A	0.30	0.50
B	0.70	0.90
C	1.45	1.75
D	-	0.50
E	0.15	0.40
G	0.80	1.00
H	1.40	1.80
J	0.00	0.10
K	0.70	1.00
L	0.37	0.48
M	0.10	0.25